

Refine Search

Search Results -

Terms	Documents
L7 and (atmospheric near pressure)	4

Database:

US Pre-Grant Publication Full-Text Database
 US Patents Full-Text Database
 US OCR Full-Text Database
 EPO Abstracts Database
 JPO Abstracts Database
 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

Search:

L8

Search History

DATE: Monday, June 21, 2004 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT; PLUR=YES; OP=ADJ</i>			
<u>L8</u>	L7 and (atmospheric near pressure)	4	<u>L8</u>
<u>L7</u>	L6 and torr	12	<u>L7</u>
<u>L6</u>	L4 and (ratio near5 oxygen)	18	<u>L6</u>
<u>L5</u>	L4 and (ratio near5 nitrogen)	5	<u>L5</u>
<u>L4</u>	L3 and (inert or argon or ar or helium or he or neon or ne or kr or xenon or xe or nitrogen)	152	<u>L4</u>
<u>L3</u>	L2 and (hf02 or zro2 or ta2o5 or tio2 or al2o3 or hfsio)	197	<u>L3</u>
<u>L2</u>	L1 and oxidation	27757	<u>L2</u>
<u>L1</u>	(oxide adj layer) or oxynitride or (high K)	63140	<u>L1</u>

END OF SEARCH HISTORY

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 4 of 4 returned.

☐ 1. Document ID: US 6569529 B1

L8: Entry 1 of 4

File: USPT

May 27, 2003

US-PAT-NO: 6569529

DOCUMENT-IDENTIFIER: US 6569529 B1

TITLE: Titanium-containing interference pigments and foils with color shifting properties

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 6197438 B1

L8: Entry 2 of 4

File: USPT

Mar 6, 2001

US-PAT-NO: 6197438

DOCUMENT-IDENTIFIER: US 6197438 B1

TITLE: Foodware with ceramic food contacting surface

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 5828080 A

L8: Entry 3 of 4

File: USPT

Oct 27, 1998

US-PAT-NO: 5828080

DOCUMENT-IDENTIFIER: US 5828080 A

TITLE: Oxide thin film, electronic device substrate and electronic device

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 5382742 A

L8: Entry 4 of 4

File: USPT

Jan 17, 1995

US-PAT-NO: 5382742

DOCUMENT-IDENTIFIER: US 5382742 A

TITLE: Gallium-containing zeolite MCM-22

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw. De
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L7 and (atmospheric near pressure)	4

Display Format: [Previous Page](#)[Next Page](#)[Go to Doc#](#)

Hit List

Search Results - Record(s) 1 through 5 of 5 returned.

☐ 1. Document ID: US 6743681 B2

L5: Entry 1 of 5

File: USPT

Jun 1, 2004

US-PAT-NO: 6743681

DOCUMENT-IDENTIFIER: US 6743681 B2

TITLE: Methods of Fabricating Gate and Storage Dielectric Stacks having Silicon-Rich-Nitride

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 6638599 B2

L5: Entry 2 of 5

File: USPT

Oct 28, 2003

US-PAT-NO: 6638599

DOCUMENT-IDENTIFIER: US 6638599 B2

TITLE: Magnetic recording medium

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 6248669 B1

L5: Entry 3 of 5

File: USPT

Jun 19, 2001

US-PAT-NO: 6248669

DOCUMENT-IDENTIFIER: US 6248669 B1

TITLE: Method for manufacturing a semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 6197438 B1

L5: Entry 4 of 5

File: USPT

Mar 6, 2001

US-PAT-NO: 6197438

DOCUMENT-IDENTIFIER: US 6197438 B1

TITLE: Foodware with ceramic food contacting surface

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw De
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☐ 5. Document ID: US 6071601 A

L5: Entry 5 of 5

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw De
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L4 and (ratio near5 nitrogen)	5

Display Format: [Previous Page](#)[Next Page](#)[Go to Doc#](#)

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 6 of 6 returned.

☐ 1. Document ID: US 6572784 B1

L9: Entry 1 of 6

File: USPT

Jun 3, 2003

US-PAT-NO: 6572784

DOCUMENT-IDENTIFIER: US 6572784 B1

TITLE: Luminescent pigments and foils with color-shifting properties

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw D
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☐ 2. Document ID: US 6521808 B1

L9: Entry 2 of 6

File: USPT

Feb 18, 2003

US-PAT-NO: 6521808

DOCUMENT-IDENTIFIER: US 6521808 B1

TITLE: Preparation and use of a catalyst for the oxidative dehydrogenation of lower alkanes

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw D
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☐ 3. Document ID: US 6461989 B1

L9: Entry 3 of 6

File: USPT

Oct 8, 2002

US-PAT-NO: 6461989

DOCUMENT-IDENTIFIER: US 6461989 B1

TITLE: Process for forming 312 phase materials and process for sintering the same

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw D
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☐ 4. Document ID: US 6071601 A

L9: Entry 4 of 6

File: USPT

Jun 6, 2000

US-PAT-NO: 6071601

DOCUMENT-IDENTIFIER: US 6071601 A

TITLE: Coated cutting tool member

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 5. Document ID: US 5795631 A

L9: Entry 5 of 6

File: USPT

Aug 18, 1998

US-PAT-NO: 5795631

DOCUMENT-IDENTIFIER: US 5795631 A

TITLE: Method of producing transparent and other electrically conductive materials

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 6. Document ID: US 5514229 A

L9: Entry 6 of 6

File: USPT

May 7, 1996

US-PAT-NO: 5514229

DOCUMENT-IDENTIFIER: US 5514229 A

TITLE: Method of producing transparent and other electrically conductive materials

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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Clear

Generate Collection

Print

Fwd Refs

Bkwd Refs

Generate OACS

Terms	Documents
L6 and microstructure	6

Display Format: TI

Change Format

[Previous Page](#)[Next Page](#)[Go to Doc#](#)

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 4 of 4 returned.

☐ 1. Document ID: US 6682826 B2

L10: Entry 1 of 4

File: USPT

Jan 27, 2004

US-PAT-NO: 6682826

DOCUMENT-IDENTIFIER: US 6682826 B2

TITLE: Magnetic recording medium, method of manufacturing therefor, and magnetic read/write apparatus

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. D.
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☐ 2. Document ID: US 5795631 A

L10: Entry 2 of 4

File: USPT

Aug 18, 1998

US-PAT-NO: 5795631

DOCUMENT-IDENTIFIER: US 5795631 A

TITLE: Method of producing transparent and other electrically conductive materials

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. D.
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☐ 3. Document ID: US 5597771 A

L10: Entry 3 of 4

File: USPT

Jan 28, 1997

US-PAT-NO: 5597771

DOCUMENT-IDENTIFIER: US 5597771 A

TITLE: Layered catalyst composite

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw. D.
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☐ 4. Document ID: US 5514229 A

L10: Entry 4 of 4

File: USPT

May 7, 1996

US-PAT-NO: 5514229

DOCUMENT-IDENTIFIER: US 5514229 A

TITLE: Method of producing transparent and other electrically conductive materials

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw. D.
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L6 and (oxygen adj containing)	4

Display Format: [Previous Page](#)[Next Page](#)[Go to Doc#](#)

[First Hit](#) [Fwd Refs](#)☐ [Generate Collection](#) [Print](#)

L11: Entry 2 of 4

File: USPT

Jul 17, 2001

DOCUMENT-IDENTIFIER: US 6261934 B1

TITLE: Dry etch process for small-geometry metal gates over thin gate dielectric

Abstract Text (1):

Fabrication of metal-on-conductive-diffusion-barrier-on-gate-dielectric structures is done by: etching the metal, by plasma-assisted anisotropic etching, down to and into the barrier metal; and then etching the remainder of the barrier layer by a dry chemical-downstream-etching process, during which the barrier layer is not exposed to ion bombardment. In the case of tungsten over titanium nitride, high selectivity and good profiles are preferably obtained, by: during the tungsten etch, using a combination of low temperature, relatively low bias, and the addition of nitrogen; and during the titanium nitride etch, using a chemical downstream etch instead of the conventional wet etch (in boiling H2SO4). (This allows better control of undercutting, and eliminates wet strip process.)

Brief Summary Text (12):

The definition of the gate electrode stack on ultra-thin (<3 nm) gate oxides for sub-tenth-micron transistors imposes a severe challenge to the etch process. Very high selectivity to SiO2 has to be achieved to avoid oxide punchthrough and subsequent damage to the silicon in the source and drain regions. Even when successfully stopped in the gate oxide, the conventional gate etch process introduces corner damage to the gate structure that needs to be annealed to guarantee good gate oxide integrity (GOI) properties of the transistor. However, it is difficult to anneal the corner damage on metal gate structures, since tungsten and titanium nitride readily oxidize in conventional oxidation processes. One solution to this problem might be to use a wet etch to slightly undercut the titanium nitride layer, moving the active gate region away from the damaged corners. However, since the selectivity of the wet etch towards tungsten is very low, the tungsten sidewall needs to be protected with a spacer prior to the titanium nitride undercut etch. This adds significant complexity to the device fabrication flow and severely reduces the process window, since the amount of undercut, and consequently the effective gate length, depends on the spacer thickness. Another approach might be to etch the titanium nitride with a process that does not cause corner damage.

Brief Summary Text (25):

No smile oxidation is required since the gate oxide is undamaged;

Detailed Description Text (32):

Following is a more extensive account of a first group of results. This group of results shows a novel all dry process for defining sub-tenth-micron W/TiN gates on ultra-thin (<3 nm) gate oxides. The process was optimized to have high selectivity to gate oxide and W eliminating the need of capping the W during TiN etch. Also, it does not introduce charge or corner damage to the gate oxide making unnecessary the gate annealing (or "smiling oxidation") after etch.

Detailed Description Text (34):

The CDE process was developed in a Mattson ASPEN II asher. The system has an inductively coupled plasma (ICP) source that generates the excited species remote from the wafer surface. Two grounded metal grids prevent charged species from

reaching the wafers assuring an isotropic process without any. charge damage. Oxygen (O₂) and hexafluoroethane (C₂F₆) were selected as process gases. A flow ratio of O₂ to C₂F₆ higher than 100 to 1 was used. Two process temperatures were investigated, 250 C. with the wafers placed on a heated chuck or room temperature with the wafers raised on three pins.

Detailed Description Text (38):

"overlap" capacitors where the edges of the top electrode were located on thick field oxide. Local oxidation of silicon (LOCOS) isolation was used for the capacitor fabrication. Three failure distributions were analyzed:

Detailed Description Text (43):

FIG. 1A shows the TiN removal as a function of the exposure time to the O₂+C₂F₆ process, for blanket TiN layers processed at 250 C. (Hot-open circles) and at room temperature (Cold-full circles). Note that the process temperature does not have a strong impact on the TiN removal process. TiN is normally etched using chlorine-based plasmas. TiO₂ is extremely non-volatile (indeed refractory) and TiF₄ is normally considered non-volatile as it sublimates at 284 C. at one atmosphere pressure. Thus, it is very surprising that the TiN removal can be adequately performed with an oxygen/fluorine ambient having a high O to F ratio, as the one used. A possible explanation for this is that the process under study is performed at low pressures (less than 2 torr) which could reduce the temperature at which TiF₄ becomes volatile to below the process temperature, resulting in the etch of the TiN film.

Detailed Description Text (69):

FIG. 5B compares the hole mobilities for pMOS devices with p+ poly- and metal-gate, as well as different gate dielectrics (3 nm of pure SiO₂, or RPNO oxynitride); all the devices have the same channel implant. Also shown is the "Universal Mobility Curve" (Universal) for holes from J. T. Watt et al. The metal-gate pMOS is observed to have slightly higher hole mobility (and closer to the universal mobility) than the p+ gate case.

Detailed Description Text (85):

For example, in alternative embodiments the preferred SiO₂ gate dielectric is replaced by oxynitride (as described in the IEDM papers cited above), or by Ta₂O₅, or by BST or PZT or other high-permittivity materials.

CLAIMS:

12. A fabrication method, comprising the steps of:

(a.) forming a gate stack layer which at least partially overlies a semiconductor region, and which includes therein

a metal conductor layer, overlying

a conductive diffusion barrier comprising titanium and nitrogen, overlying

a gate dielectric which provides capacitive coupling to said semiconductor region; and

(b.) etching said gate stack layer in a pattern, using a process which includes the substeps of:

(i.) etching the metal, by plasma-assisted anisotropic etching, down to and into the barrier metal, and then

(ii.) etching the remainder of the barrier layer by a dry chemical-downstream-etching process which includes oxygen and fluorine sources, and substantially no

Hit List

Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs
Generate OACS				

Search Results - Record(s) 1 through 4 of 4 returned.

☐ 1. Document ID: US 6444542 B2

L11: Entry 1 of 4

File: USPT

Sep 3, 2002

US-PAT-NO: 6444542

DOCUMENT-IDENTIFIER: US 6444542 B2

TITLE: Integrated circuit and method

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMNC	Draw D
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☐ 2. Document ID: US 6261934 B1

L11: Entry 2 of 4

File: USPT

Jul 17, 2001

US-PAT-NO: 6261934

DOCUMENT-IDENTIFIER: US 6261934 B1

TITLE: Dry etch process for small-geometry metal gates over thin gate dielectric

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMNC	Draw D
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☐ 3. Document ID: US 6211035 B1

L11: Entry 3 of 4

File: USPT

Apr 3, 2001

US-PAT-NO: 6211035

DOCUMENT-IDENTIFIER: US 6211035 B1

TITLE: Integrated circuit and method

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMNC	Draw D
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☐ 4. Document ID: US 5983906 A

L11: Entry 4 of 4

File: USPT

Nov 16, 1999

US-PAT-NO: 5983906

DOCUMENT-IDENTIFIER: US 5983906 A

TITLE: Methods and apparatus for a cleaning process in a high temperature, corrosive, plasma environment

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWIC	Draw. Des
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Clear	Generate Collection	Print	Fwd Refs	Bkwd Refs	Generate OACS
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Terms	Documents
L4 and (flow adj ratio)	4

Display Format:

[Previous Page](#)

[Next Page](#)

[Go to Doc#](#)